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Search	L No.	Hits	Text Search		Data Bases
Dear Con	200 m - 21, V - 200 m		(257/18,22,85,94,103,190,200,201).CCL		USPAT; EPO; JPO
IS&R	LI	2802	S	7/15/02 14:45	
Back			algainnasp algainasnp algainpasn		USPAT; EPO; JPO
BRS	L5	3	gaalinnasp gaalinasnp gaalinpasn	7/15/02 15:26	
DRO		 			USPAT; EPO; JPO
BRS	L8	53	1 and gan adj substrate	7/15/02 15:27	Derwent; IBM TD
DIG	20		gaalinnasp gaalinasnp gaalinpasn		USPAT; EPO; JPC
BRS	L9	19	inalganasp inalgaasnp inalgapasn	7/15/02 15:18	Derwent; IBM TD
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BRS	L10	11	9 and @ay<2000	7/15/02 15:27	Derwent; IBM TD
DRS	LIU	 	algainnasp algainasnp algainpasn		USPAT; EPO; JPO
BRS	LII	2910	gaalinnasp gaalinasnp gaalinpasn	7/15/02 15:26	Derwent; IBM TD
DRS	- 3	1 27.0			USPAT; EPO; JPO
BRS	L12	64	11 and gan adj substrate	7/15/02 15:27	Derwent; IBM TD
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BRS	L13	32	12 and @ay<2000	7/15/02 15:27	Derwent; IBM TD
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Search Result	SOLIDARIO NALIO PERSONANO	Annual Vision of Control	and the second s	Cl/Sub	Cl/Sub	Inventor
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A1	20011206	10	AND SEMICONDUCTOR DEVICE	257/103	372/43	MORITA, ETSUO et al.
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U3 03/01/0 B1	20020405		Method for manufacturing gallium			
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L Number	Hits	Search Text	DB	Time stamp
1	2802	(257/18,22,85,94,103,190,200,201).CCLS.	USPAT;	2002/07/15 14:45
-	2002	(300, 20, 20, 20, 20, 20, 20, 20, 20, 20,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	İ
	3	algainnasp algainasnp algainpasn	USPAT;	2002/07/15 14:53
5	3	gaalinnasp gaalinasnp gaalinpasn	US-PGPUB;	
		inalganasp inalgaasnp inalgapasn	EPO; JPO;	
		alinganasp alingaasnp alingapasn	DERWENT;	
		alinganasp alingadshp alingapash	IBM TDB	
		gainalnasp gainalasnp gainalpasn	IBM_IDB	
		ingaalnasp ingaalasnp ingaalpasn	HCDAM.	2002/07/15 15:17
8	53	((257/18,22,85,94,103,190,200,201).CCLS.)	USPAT;	2002/07/13 13:17
		and gan adj substrate	US-PGPUB;	
			EPO; JPO;	
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			IBM_TDB	0000/07/15 15-10
9	19	(((257/18,22,85,94,103,190,200,201).CCLS.)	USPAT;	2002/07/15 15:18
		and gan adj substrate) and (algainnasp	US-PGPUB;	
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		alingaasnp alingapasn gainalnasp		
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		inalganp inalganp alinganasp		
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		inalgap)		
1.0	1.1	((((257/18,22,85,94,103,190,200,201).CCLS.)	USPAT;	2002/07/15 15:18
10	11	and gan adj substrate) and (algainnasp	US-PGPUB;	
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		inalgaasnp inalgapasn alinganasp	1011_100	
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